AMENDMENTS TO THE CLAIMS

Please amend Claims 1, 3, 18 and 19 as indicated below.

1. (Currently Amended) A process of growing a thin film of Al_2O_3 on a substrate in a reaction chamber by a sequential vapor deposition process comprising a plurality of cycles, each cycle comprising:

exposing the ~~part~~ substrate in the reaction chamber to gaseous trimethyl aluminum (TMA);

stopping provision of the gaseous TMA;

removing gaseous TMA from the reaction chamber;

exposing the ~~part~~ substrate in the reaction chamber to atomic oxygen; and

removing atomic oxygen from the reaction chamber,

wherein in each cycle more than one monolayer of Al_2O_3 is formed.

2. (Original) The process of claim 1, wherein in each cycle a layer of Al_2O_3 3 Å thick is formed.

3. (Currently Amended) The process of Claim 1, wherein the atomic oxygen is ~~radicals are~~ generated remotely in a radical generator.

4. (Original) The process of Claim 1, wherein the process is carried out at room temperature.

5. - 17. (Cancelled)

18. (Currently Amended) A process of growing a thin film of Al_2O_3 on a substrate in a reaction chamber by a sequential vapor deposition process comprising a plurality of cycles, each cycle comprising:

exposing the ~~part~~ substrate in the reaction chamber to gaseous trimethyl aluminum (TMA);

stopping provision of the gaseous TMA;

removing gaseous TMA from the reaction chamber; and

exposing the ~~part~~ substrate in the reaction chamber to atomic oxygen.

19. (Currently Amended) The process of Claim 18, wherein the atomic oxygen is ~~radicals are~~ generated remotely in a radical generator.

20. (Previously Presented) The process of Claim 18, wherein the process is carried out at room temperature.